



# BM8U060AG

60V, 20A<sup>(1)</sup>, PMR series Schottky

## Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	2997 $\mu\text{m}$	118 mil
	Top Metal Pad Size (B)	2827 $\mu\text{m}$	111.3 mil
	Passivation Seal (C)	2927 $\mu\text{m}$	115.2 mil
	Wafer Thickness (D)	254 $\pm$ 15 $\mu\text{m}$	10 $\pm$ 0.6 mil
	Scribe Line Width (E)	70 $\mu\text{m}$	2.76 mil
	Wafer Diameter	6 inch	
	Gross Die	1695	
	Top Side Metallization/ Layer Thickness	Ag / 3 $\pm$ 0.3 $\mu\text{m}$	
	Back Side Metallization/ Layer Thickness	Ag / 2 $\pm$ 0.2 $\mu\text{m}$	
	Recommended Storage Environment	Store in original container, in dry nitrogen, (6 months at an ambient temperature of 23 $^{\circ}$ C $\pm$ 3 $^{\circ}$ C)	

## Electrical Characteristics in C/P test ( $T_J = 25^{\circ}\text{C}$ )

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{BR}$	Reverse Breakdown Voltage	60	—	—	V	$I_R = 300\mu\text{A}$
$V_F$	Instantaneous Forward Voltage	—	0.345	0.37	V	$I_F = 3\text{A}^{(2)}$
		—	0.455	0.49	V	$I_F = 10\text{A}^{(2)}$
$I_R$	Reverse Leakage Current	—	100	150	$\mu\text{A}$	$V_R = 60\text{V}$
$T_J, T_{STG}$	Operating and Storage Temperature	-40 $^{\circ}$ C to 150 $^{\circ}$ C Max				